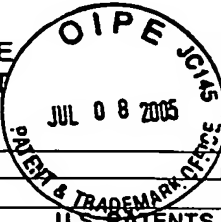


**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

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**Complete if Known**

Application Number	10/825,647
Filing Date	April 15, 2004
First Named Inventor	David B. Slater, Jr.
Group Art Unit	2822
Examiner Name	Amir Zarabian
Attorney Docket Number	5308-231DV

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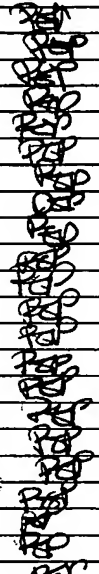
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Substitute form 1449A/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/825,647
		Filing Date	April 15, 2004
		First Named Inventor	David B. Slater, Jr.
		Group Art Unit	2822
		Examiner Name	Amir Zarabian
Sheet	Page 2 of 3	Attorney Docket Number	5308-231DV

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Sheet	Page 3 of 3	Attorney Docket Number	5308-231DV

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